Document Number: MRF18060A
Rev. 11, 10/2008

RoHS

RF Power Field Effect Transistor

N-Channel Enhancement-Mode Lateral MOSFET

MRF18060ALR3

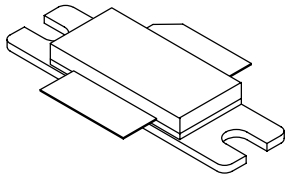
**1805-1880 MHz, 60 W, 26 V
LATERAL N-CHANNEL
RF POWER MOSFET**

Designed for PCN and PCS base station applications with frequencies from 1800 to 2000 MHz. Suitable for FM, TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN-PCS/cellular radio and WLL applications.

- Typical GSM Performance @ 1805 MHz
  Power Gain — 13 dB @ 60 Watts
  Efficiency — 45% @ 60 Watts
- Capable of Handling 10:1 VSWR, @ 26 Vdc, 1840 MHz, 60 Watts CW Output Power

Features

- Internally Matched for Ease of Use
- High Gain, High Efficiency and High Linearity
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Excellent Thermal Stability
- Available with Low Gold Plating Thickness on Leads. L Suffix Indicates 40μ″ Nominal.
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.



**CASE 465-06, STYLE 1
NI-780**

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +15	Vdc
Total Device Dissipation @ $T_C \geq 25°C$ Derate above 25°C	P_D	180 1.03	W W/°C
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature	T_J	200	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.97	°C/W

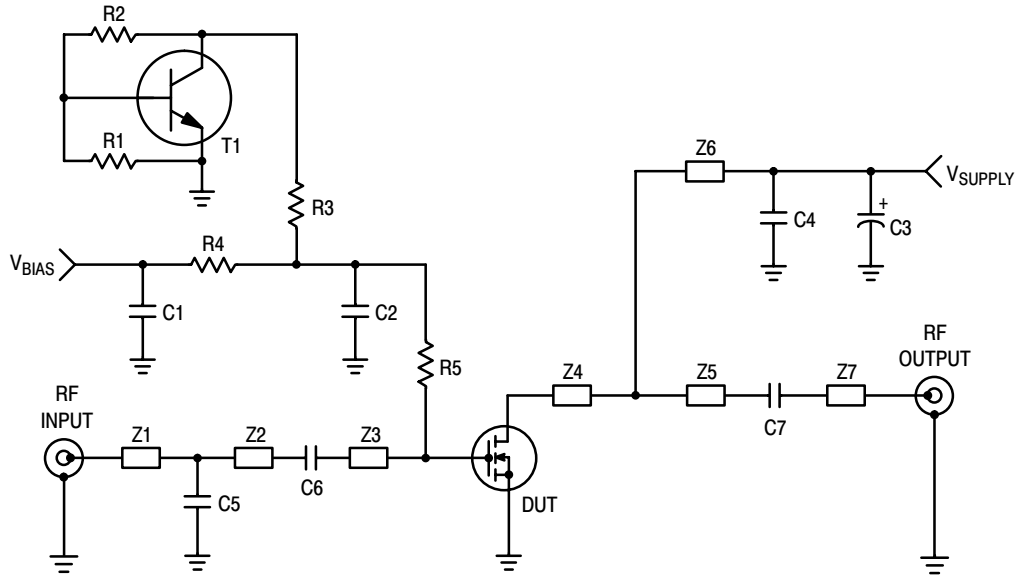
Table 3. ESD Protection Characteristics

Test Conditions	Class
Human Body Model	2 (Minimum)
Machine Model	M3 (Minimum)

Table 4. Electrical Characteristics (T_C = 25°C unless otherwise noted)

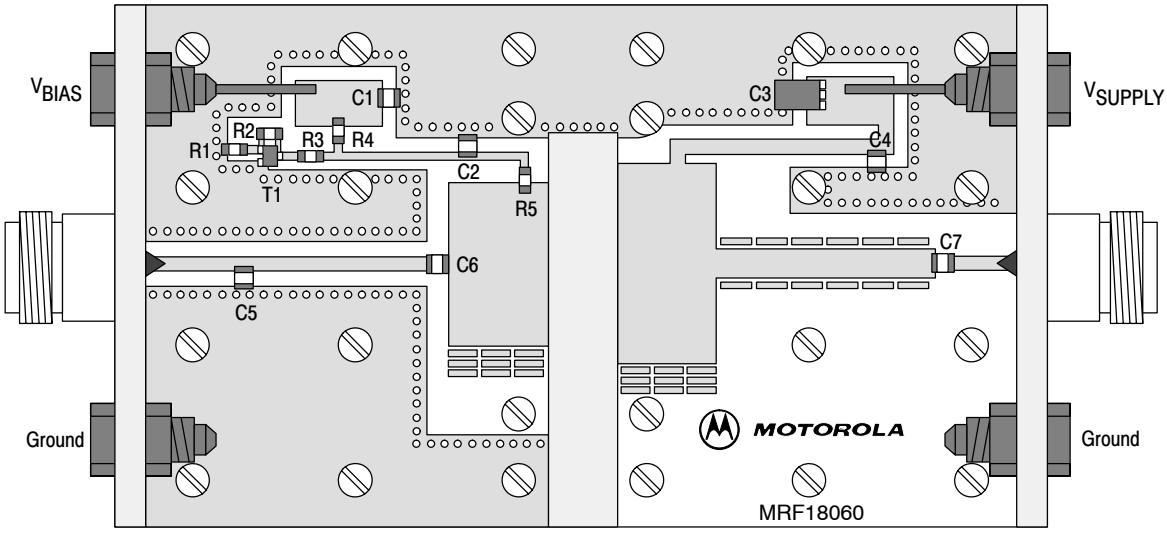
Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Drain-Source Breakdown Voltage (V_{GS} = 0 Vdc, I_D = 10 μAdc)	$V_{(BR)DSS}$	65	—	—	Vdc
Zero Gate Voltage Drain Current (V_{DS} = 26 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	6	μAdc
Gate-Source Leakage Current (V_{GS} = 5 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	—	—	1	μAdc
On Characteristics					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 300 μAdc)	$V_{GS(th)}$	2	—	4	Vdc
Gate Quiescent Voltage (V_{DS} = 26 Vdc, I_D = 500 mAdc)	$V_{GS(Q)}$	2.5	3.9	4.5	Vdc
Drain-Source On-Voltage (V_{GS} = 10 Vdc, I_D = 2 Adc)	$V_{DS(on)}$	—	0.27	—	Vdc
Dynamic Characteristics					
Input Capacitance (Including Input Matching Capacitor in Package) (1) (V_{DS} = 26 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{iss}	—	160	—	pF
Output Capacitance (1) (V_{DS} = 26 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{oss}	—	740	—	pF
Reverse Transfer Capacitance (V_{DS} = 26 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{rss}	—	2.7	—	pF
Functional Tests (In Freescale Test Fixture, 50 ohm system)					
Common-Source Amplifier Power Gain @ 60 W (V_{DD} = 26 Vdc, I_{DQ} = 500 mA, f = 1805 MHz)	G_{ps}	11.5	13	—	dB
Drain Efficiency @ 60 W (V_{DD} = 26 Vdc, I_{DQ} = 500 mA, f = 1805 MHz)	η	43	45	—	%
Input Return Loss (V_{DD} = 26 Vdc, P_{out} = 60 W CW, I_{DQ} = 500 mA, f = 1805 MHz)	IRL	—	—	- 10	dB

1. Part is internally matched both on input and output.



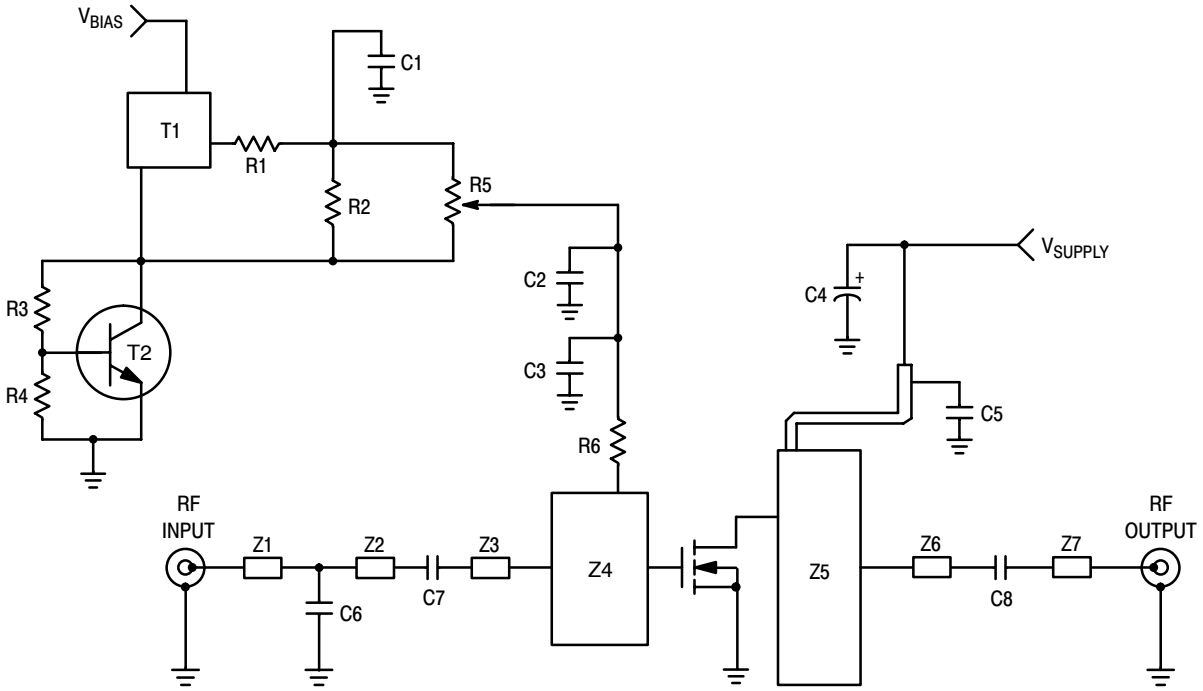
C1	100 nF Chip Capacitor (1203)	Z1	0.47″ x 0.09″ Microstrip
C2, C4, C7	10 pF Chip Capacitors	Z2	1.16″ x 0.09″ Microstrip
C3	10 μF, 35 V Electrolytic Capacitor	Z3	0.57″ x 0.95″ Microstrip
C5	1.2 pF Chip Capacitor	Z4	0.59″ x 1.18″ Microstrip
C6	1.0 pF Chip Capacitor	Z5	1.26″ x 0.15″ Microstrip
R1, R3	2.2 kΩ Chip Resistors (0805)	Z6	1.15″ x 0.09″ Microstrip
R2, R4	2.7 kΩ Chip Resistors (0805)	Z7	0.37″ x 0.09″ Microstrip
R5	1.1 kΩ Chip Resistor (0805)		
T1	BC847 Transistor SOT-23		

Figure 1. 1805 - 1880 MHz Test Fixture Schematic



Freescale has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescale Semiconductor signature/logo. PCBs may have either Motorola or Freescale markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. 1805 - 1880 MHz Test Fixture Component Layout



C1	1 μF Chip Capacitor (0805)	T1	LP2951 Micro-8 Voltage Regulator
C2	100 nF Chip Capacitor (0805)	T2	BC847 SOT-23 NPN Transistor
C3, C5, C8	10 pF Chip Capacitors, ACCU-P (0805)	Z1	0.159″ x 0.055″ Microstrip
C4	10 μF, 35 V Electrolytic Capacitor	Z2	0.982″ x 0.055″ Microstrip
C6	1.8 pF Chip Capacitor, ACCU-P (0805)	Z3	0.087″ x 0.055″ Microstrip
C7	1 pF Chip Capacitor, ACCU-P (0805)	Z4	0.512″ x 0.787″ Microstrip
R1	10 Ω Chip Resistor (0805)	Z5	0.433″ x 1.220″ Microstrip
R2, R6	1 kΩ Chip Resistors (0805)	Z6	1.039″ x 0.118″ Microstrip
R3	1.2 kΩ Chip Resistor (0805)	Z7	0.268″ x 0.055″ Microstrip
R4	2.2 kΩ Chip Resistor (0805)	Substrate = 0.5 mm Teflon® Glass, ε_r = 2.55	
R5	5 kΩ, SMD Potentiometer		

Figure 3. 1800 - 2000 MHz Demo Board Schematic

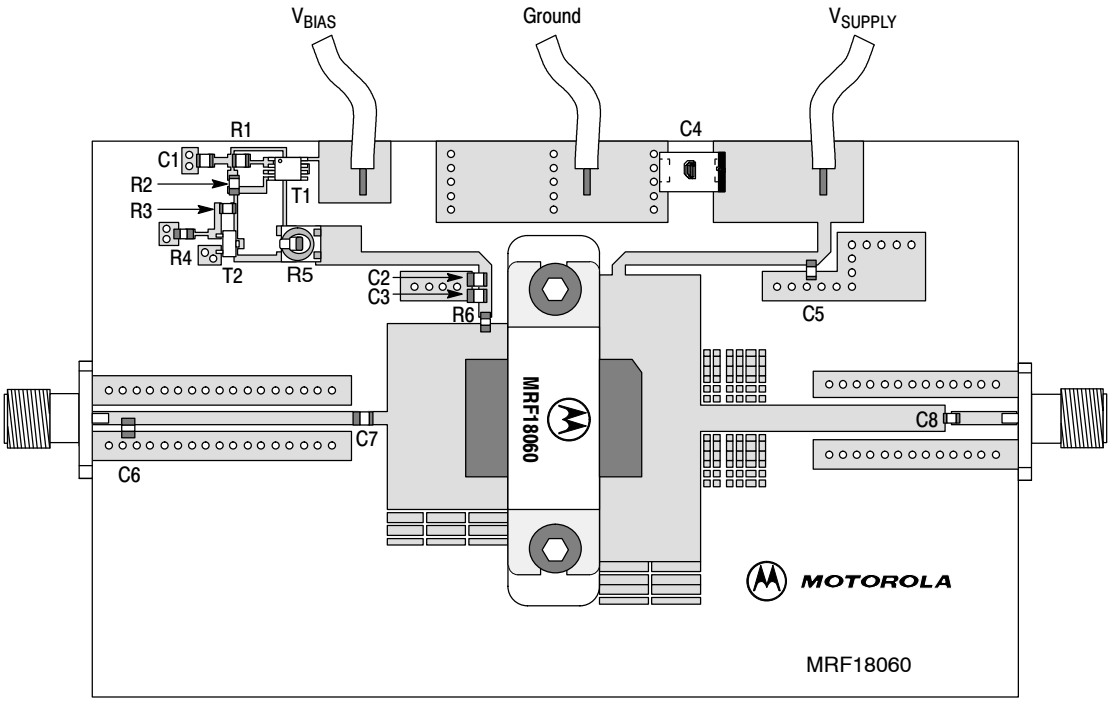


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Figure 4. 1800 - 2000 MHz Demo Board Component Layout

TYPICAL CHARACTERISTICS (DATA TAKEN USING WIDEBAND DEMONSTRATION BOARD)

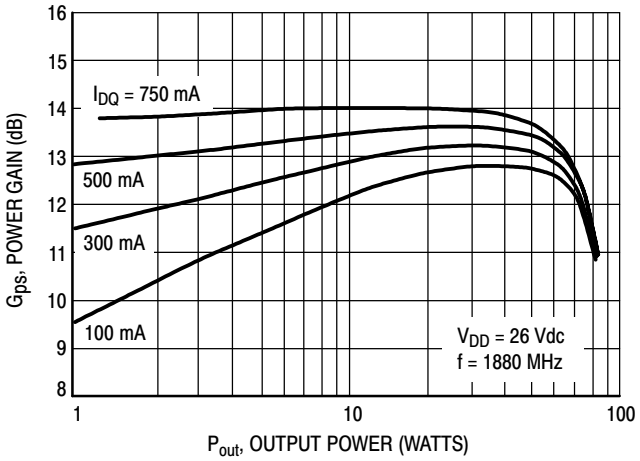


Figure 5. Power Gain versus Output Power

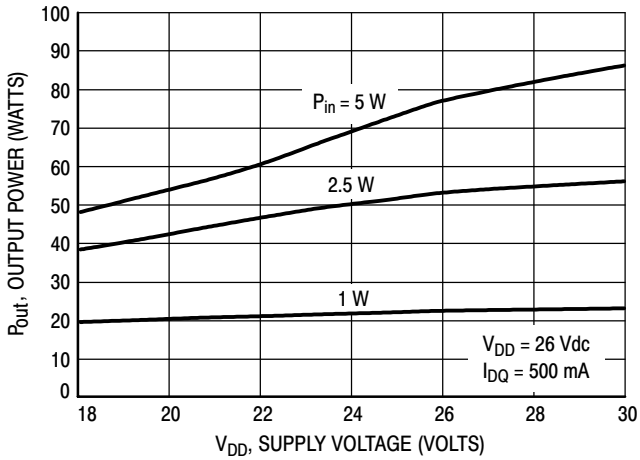


Figure 6. Output Power versus Supply Voltage

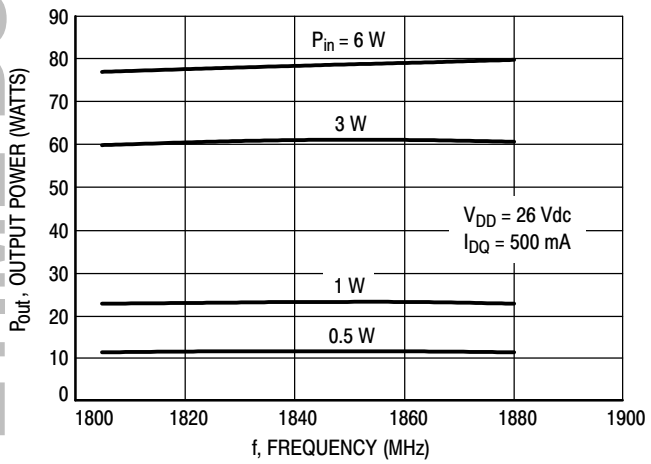


Figure 7. Output Power versus Frequency

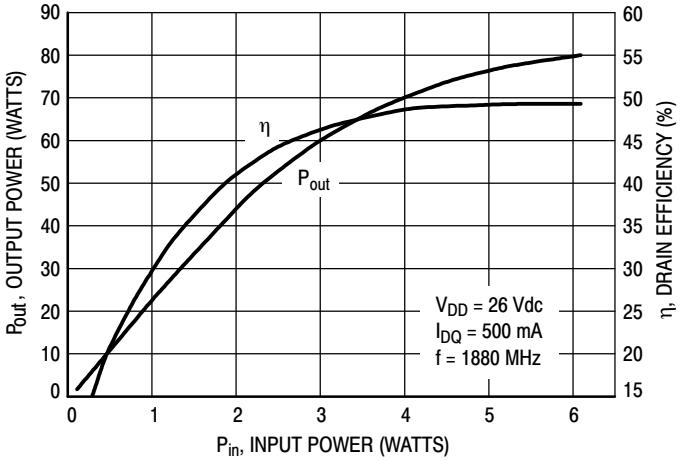


Figure 8. Output Power and Efficiency versus Input Power

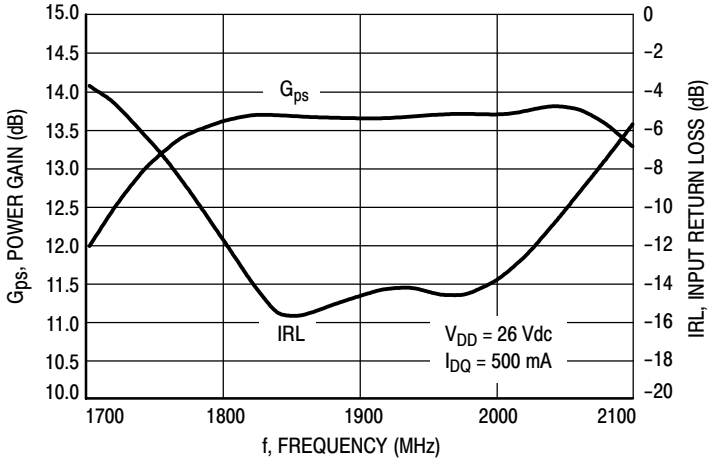
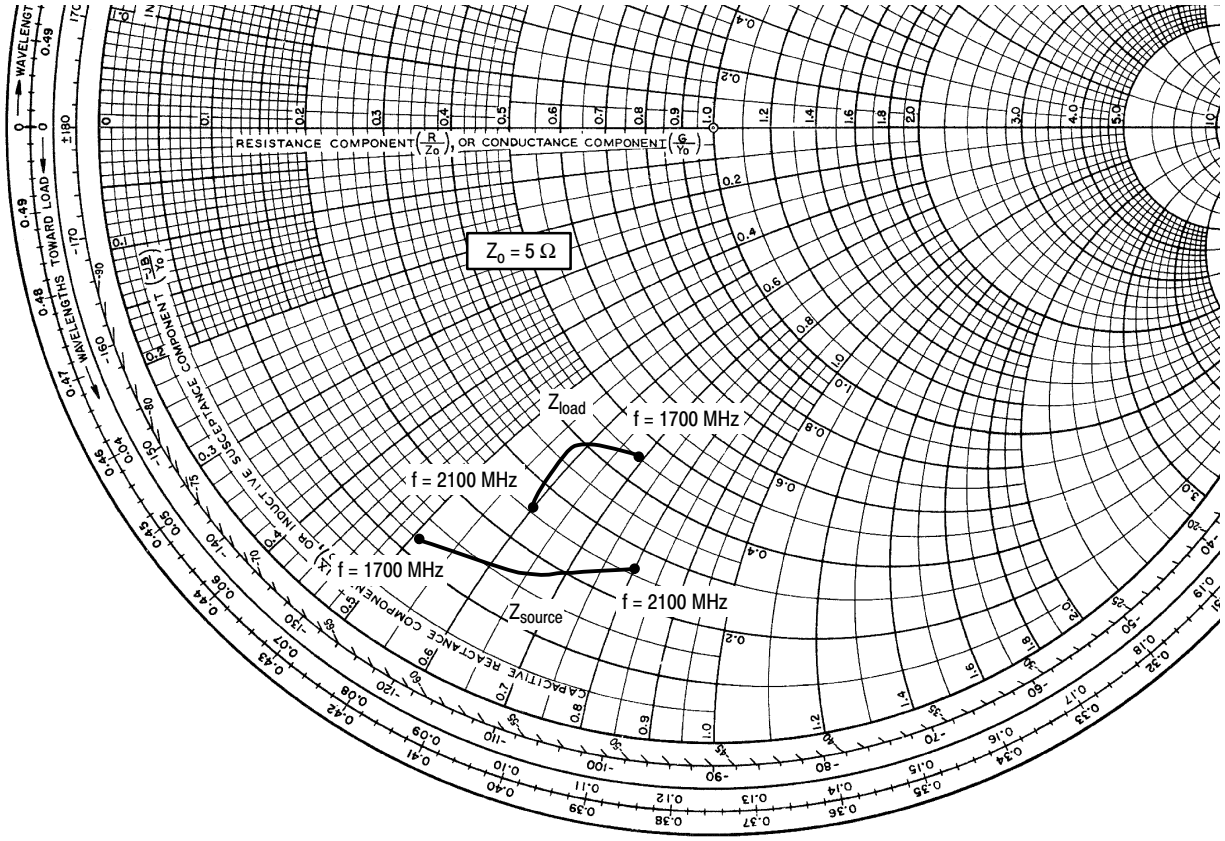


Figure 9. Wideband Gain and IRL (at Small Signal)



V_{DD} = 26 V, I_{DQ} = 500 mA, P_{out} = 60 W CW

f MHz	Z_{source} Ω	Z_{load} Ω
1700	0.60 - j2.53	2.27 - j3.44
1800	0.80 - j3.20	2.05 - j3.05
1900	0.92 - j3.42	1.90 - j2.90
2000	1.07 - j3.59	1.64 - j2.88
2100	1.31 - j4.00	1.29 - j2.99

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

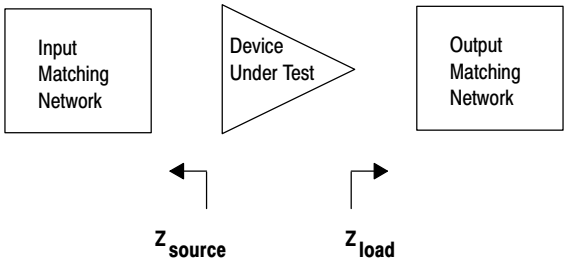
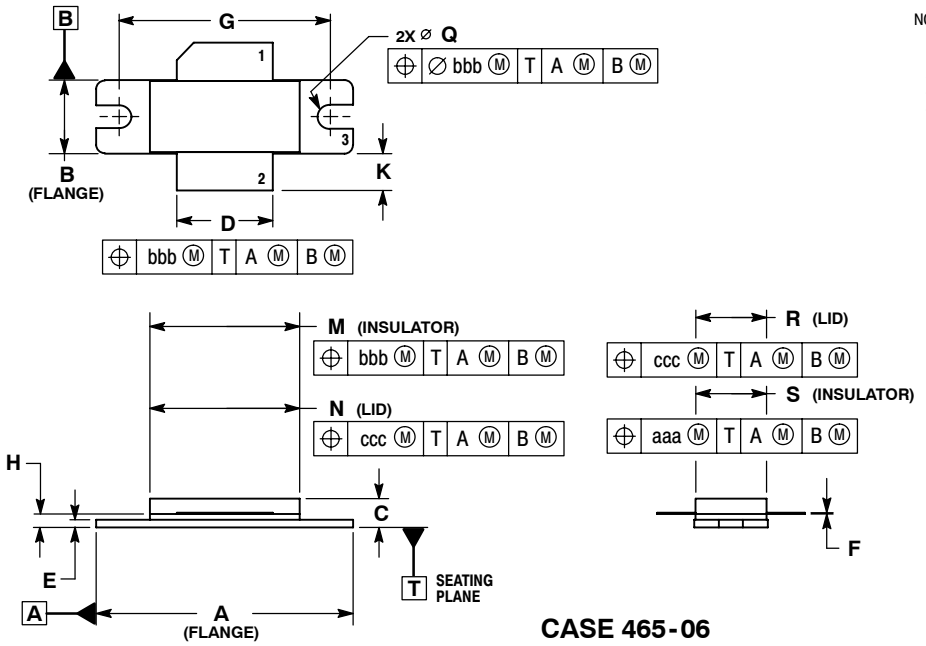


Figure 10. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M–1994.
2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.66	19.96
N	0.772	0.788	19.60	20.00
Q	⌀.118	⌀.138	⌀3.00	⌀3.51
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

CASE 465-06
ISSUE G
NI-780
MRF18060ALR3

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
11	Oct. 2008	• Data sheet revised to reflect part status change, p. 1, including use of applicable overlay. • Modified data sheet to reflect RF Test Reduction described in Product and Process Change Notification number, PCN12779, p. 1, 2 • Added Product Documentation and Revision History, p. 9

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Japan:
Freescale Semiconductor Japan Ltd.
Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku,
Tokyo 153-0064
Japan
0120 191014 or +81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:
Freescale Semiconductor China Ltd.
Exchange Building 23F
No. 118 Jianguo Road
Chaoyang District
Beijing 100022
China
+86 10 5879 8000
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Fax: +1-303-675-2150
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